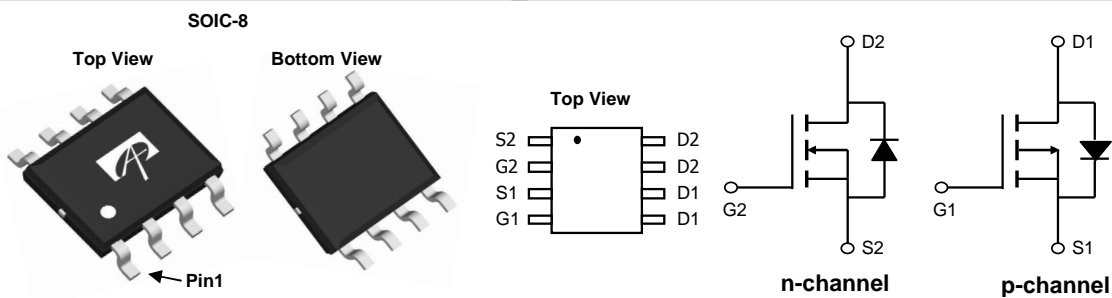


### General Description

The AO4611 uses advanced trench technology MOSFETs to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

### Product Summary

N-Channel	P-Channel
$V_{DS} (V) = 60V$	-60V
$I_D = 6.3A (V_{GS}=10V)$	-4.9A
$R_{DS(ON)}$	
< 25m $\Omega$ ( $V_{GS}=10V$ )	< 42m $\Omega$ ( $V_{GS} = -10V$ )
< 30m $\Omega$ ( $V_{GS}=4.5V$ )	< 52m $\Omega$ ( $V_{GS} = -4.5V$ )
100% UIS Tested	100% UIS Tested
100% Rg Tested	100% Rg Tested



### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	$V_{DS}$	60	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$	6.3	-4.9	A
	$T_A=70^\circ C$	5	-3.9	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	40	-30	
Power Dissipation	$T_A=25^\circ C$	2	2	W
	$T_A=70^\circ C$	1.28	1.28	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$

### Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	n-ch	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		n-ch	74	110	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	n-ch	35	60	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	p-ch	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		p-ch	74	110	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	p-ch	35	40	$^\circ C/W$

N Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	60			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=48\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1.5	2.1	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=6.3\text{A}$ $T_J=125^\circ\text{C}$		20 34	25 42	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=5.7\text{A}$		22	30	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}, I_D=6.3\text{A}$		27		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.74	1	V
$I_S$	Maximum Body-Diode Continuous Current				3	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$		1920	2300	pF
$C_{oss}$	Output Capacitance			155		pF
$C_{rss}$	Reverse Transfer Capacitance			116		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		0.65	0.8	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, I_D=6.3\text{A}$		47.6	58	nC
$Q_g(4.5\text{V})$	Total Gate Charge			24.2	30	nC
$Q_{gs}$	Gate Source Charge			6		nC
$Q_{gd}$	Gate Drain Charge			14.4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, R_L=4.7\Omega,$ $R_{GEN}=3\Omega$		7.6		ns
$t_r$	Turn-On Rise Time			5		ns
$t_{D(off)}$	Turn-Off DelayTime			28.9		ns
$t_f$	Turn-Off Fall Time			5.5		ns
$t_{rr}$	Body Diode Reverse Recovery Time		$I_F=6.3\text{A}, di/dt=100\text{A}/\mu\text{s}$		33.2	40
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=6.3\text{A}, di/dt=100\text{A}/\mu\text{s}$		43		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using  $<300 \mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating. Rev5: Nov. 2010

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

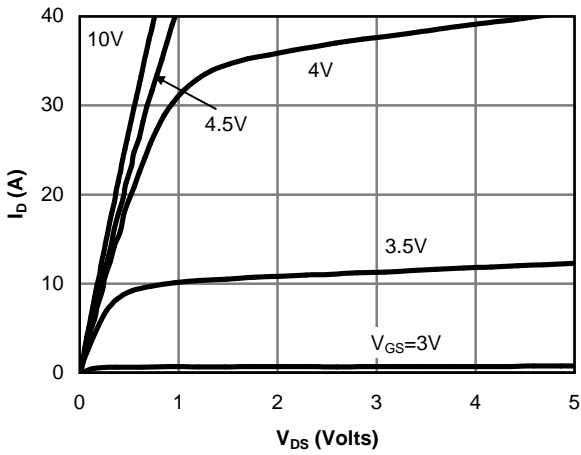


Fig 1: On-Region Characteristics

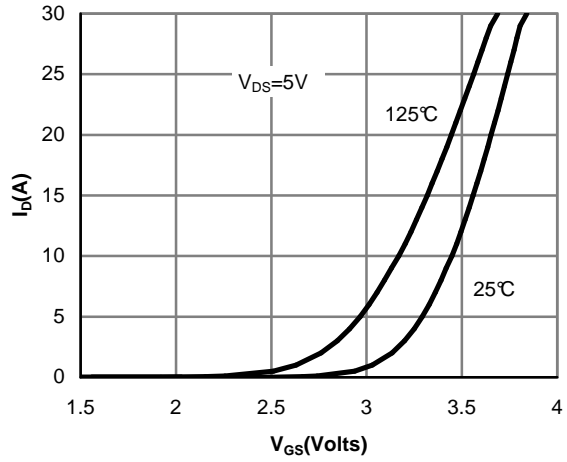


Figure 2: Transfer Characteristics

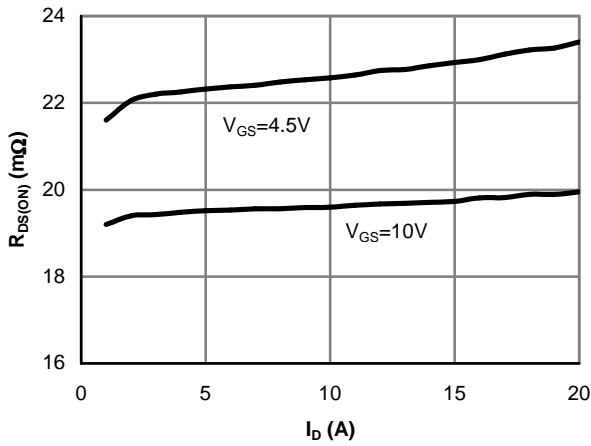


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

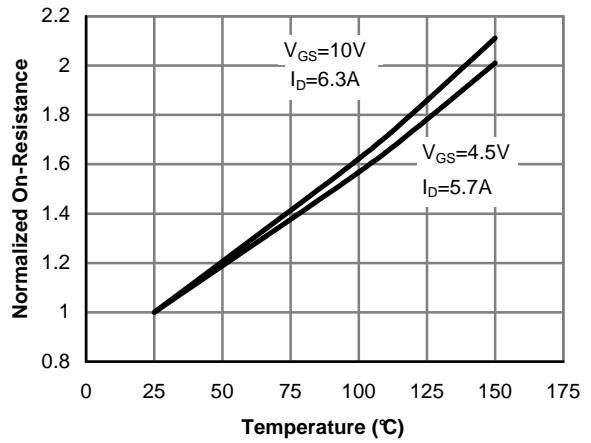


Figure 4: On-Resistance vs. Junction Temperature

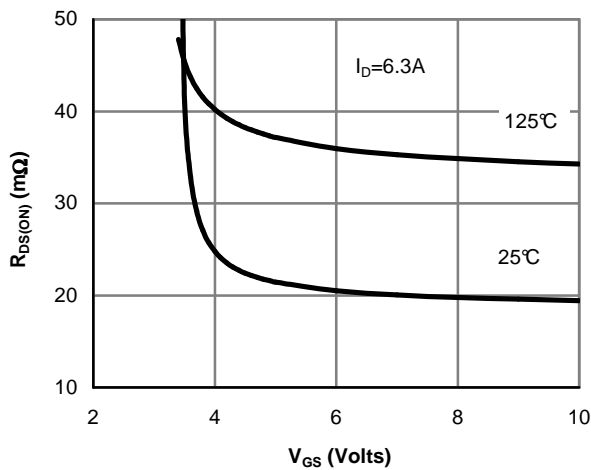


Figure 5: On-Resistance vs. Gate-Source Voltage

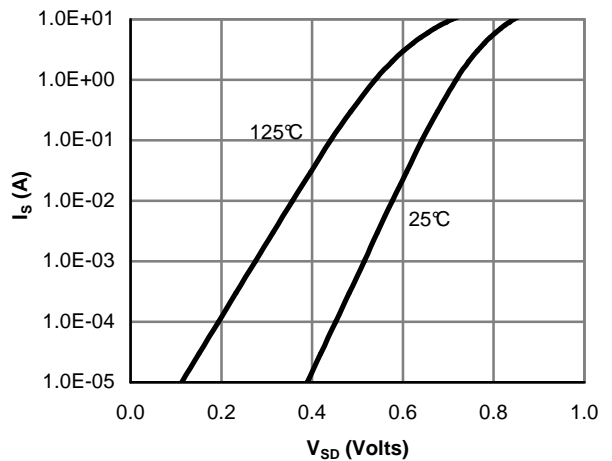


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

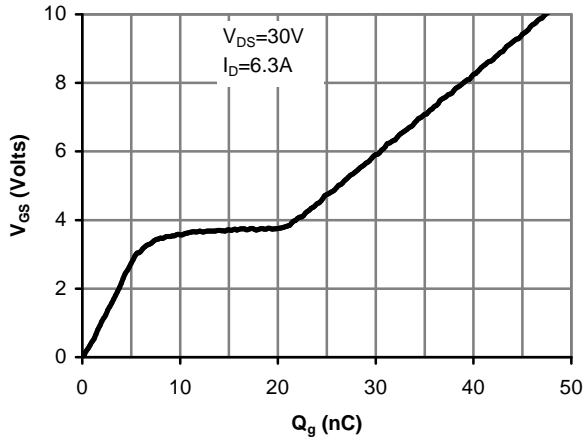


Figure 7: Gate-Charge Characteristics

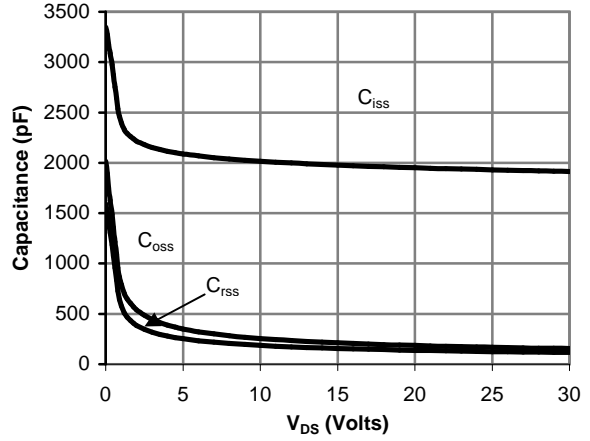


Figure 8: Capacitance Characteristics

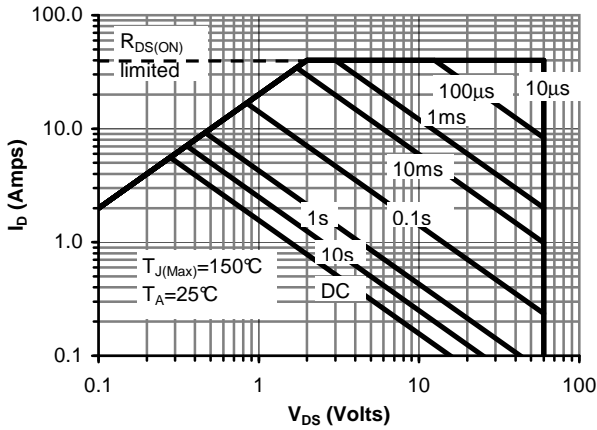


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

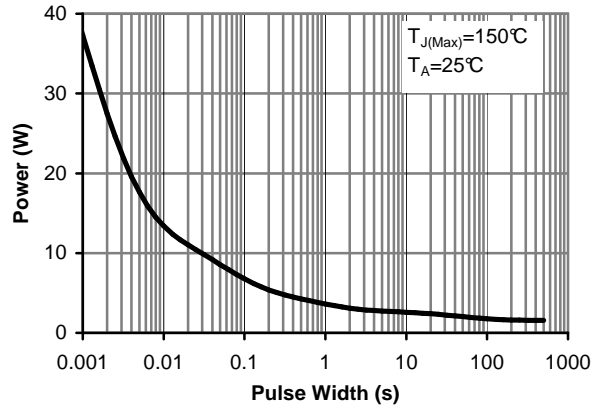


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

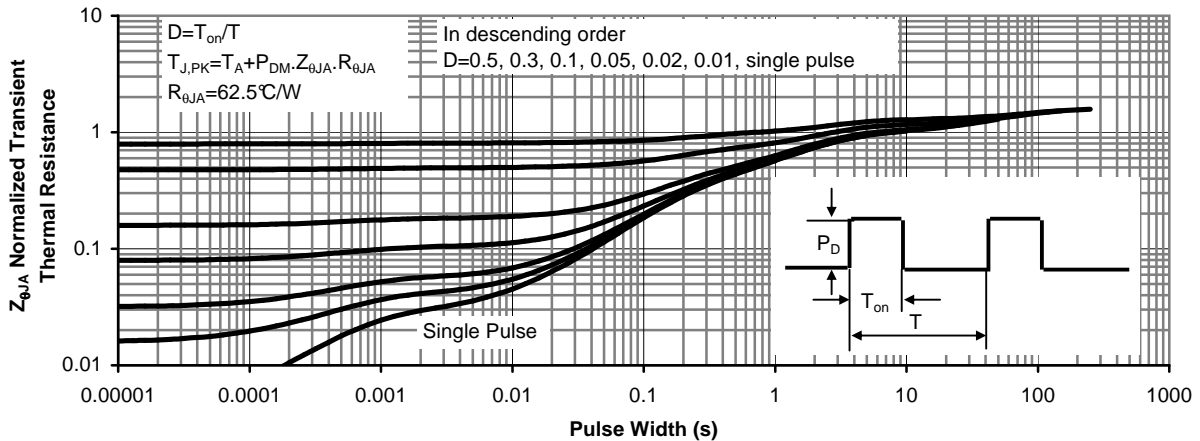


Figure 11: Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-60			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-48\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.5	-1.9	-3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	-30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-4.9\text{A}$ $T_J=125^\circ\text{C}$		34	42	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-4.4\text{A}$		42	52	
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-4.9\text{A}$		17.8		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.73	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-3	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-30\text{V}, f=1\text{MHz}$		2417	2900	pF
$C_{oss}$	Output Capacitance			179		pF
$C_{rss}$	Reverse Transfer Capacitance			120		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		1.9	2.3	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}, V_{DS}=-30\text{V}, I_D=-4.9\text{A}$		45.2	55	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			22.8	28	nC
$Q_{gs}$	Gate Source Charge			5.8		nC
$Q_{gd}$	Gate Drain Charge			9.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}, V_{DS}=-30\text{V}, R_L=6.2\Omega,$ $R_{GEN}=3\Omega$		9.8		ns
$t_r$	Turn-On Rise Time			6.1		ns
$t_{D(off)}$	Turn-Off DelayTime			44		ns
$t_f$	Turn-Off Fall Time			12.7		ns
$t_{rr}$	Body Diode Reverse Recovery Time		$I_F=-4.9\text{A}, dI/dt=100\text{A}/\mu\text{s}$		32	42
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-4.9\text{A}, dI/dt=100\text{A}/\mu\text{s}$		42		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating. Rev5: Nov. 2010

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

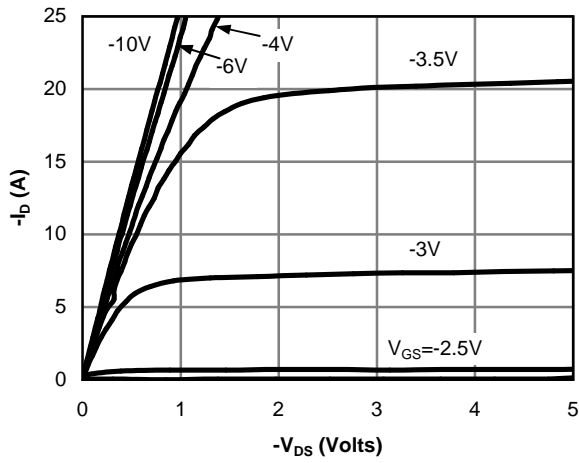


Fig 1: On-Region Characteristics

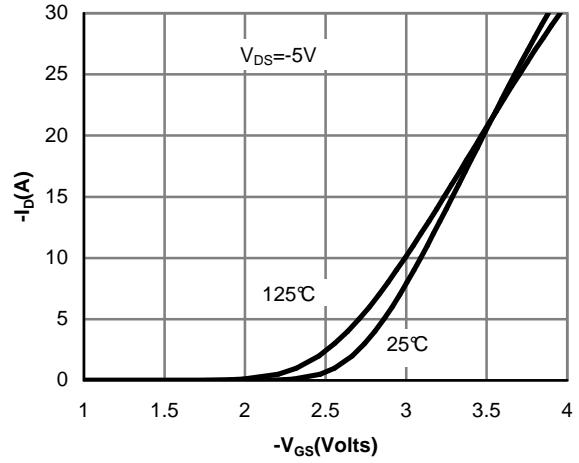


Figure 2: Transfer Characteristics

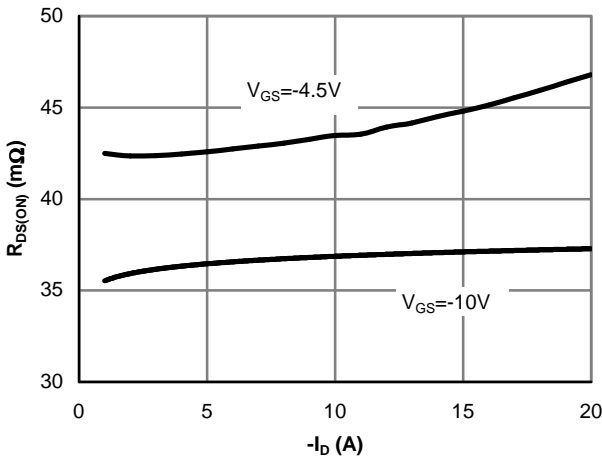


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

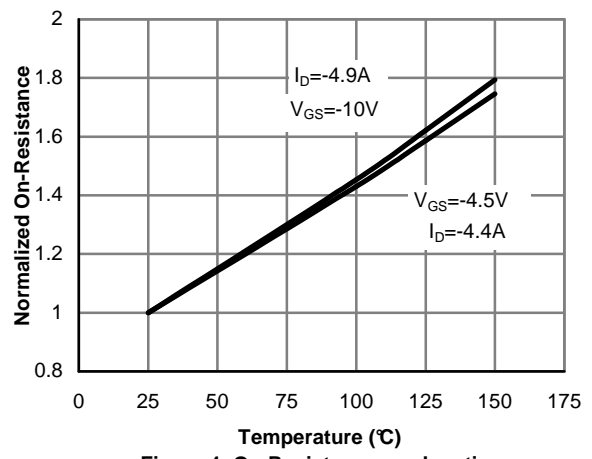


Figure 4: On-Resistance vs. Junction Temperature

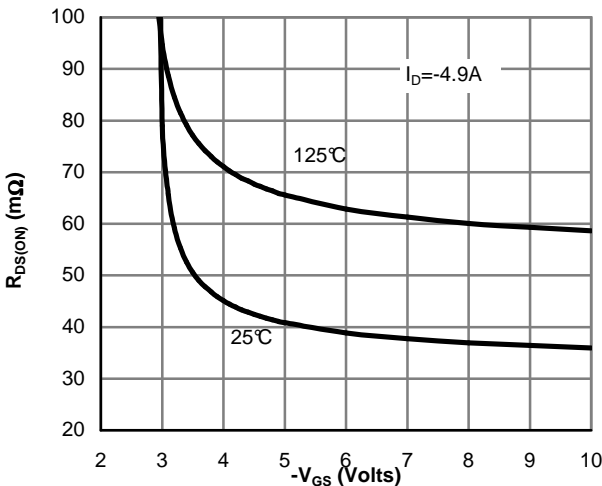


Figure 5: On-Resistance vs. Gate-Source Voltage

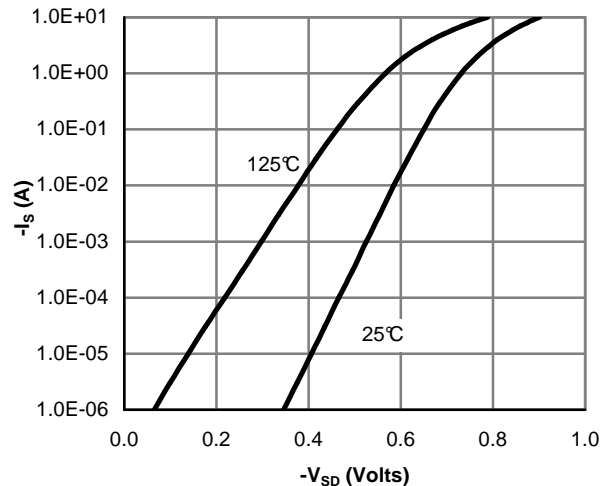


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

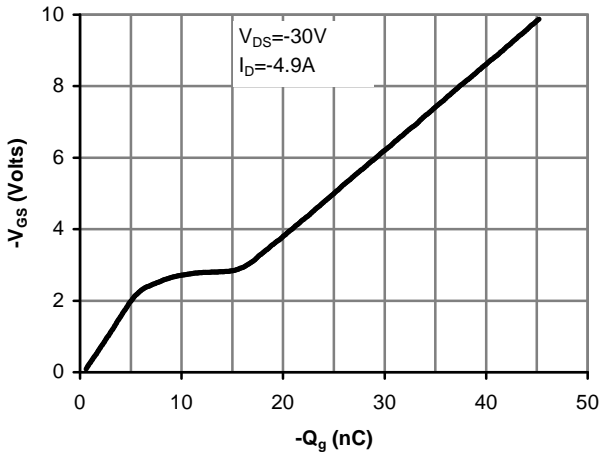


Figure 7: Gate-Charge Characteristics

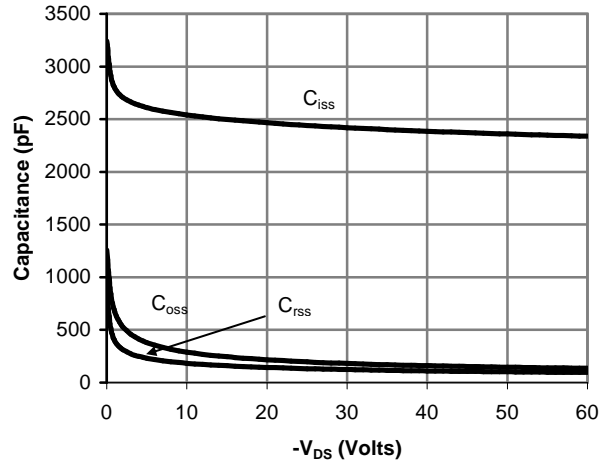


Figure 8: Capacitance Characteristics

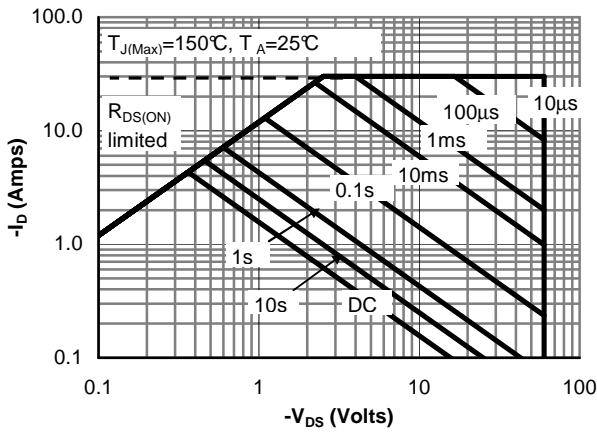


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

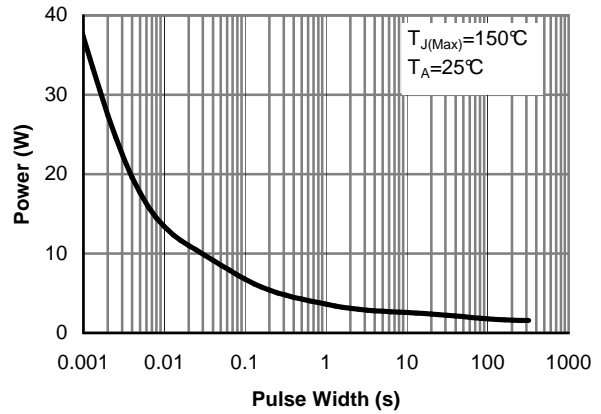


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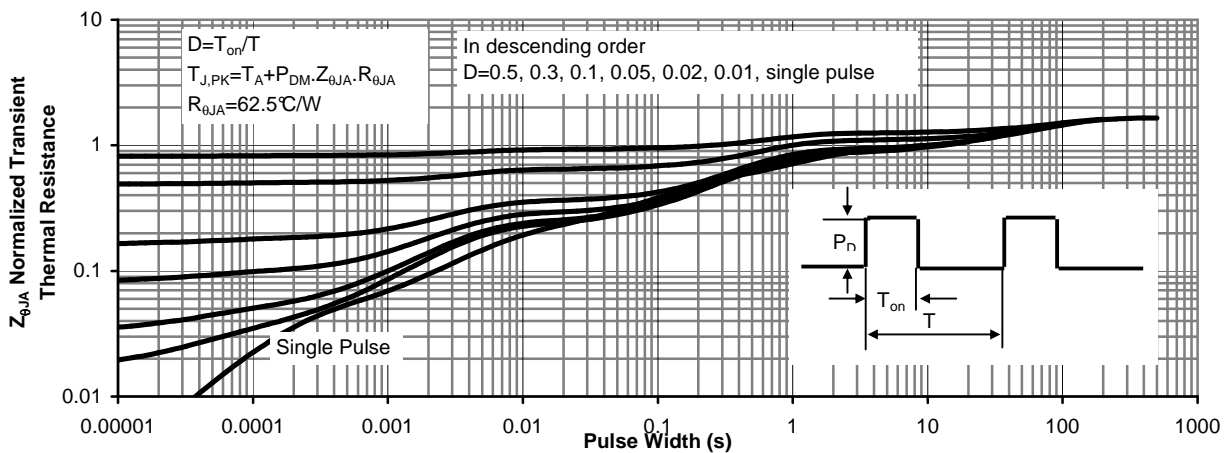


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